

# Bipolar Power Transistors

## PNP Silicon

### NJT4030P, NJV4030P

#### Features

- Epoxy Meets UL 94, V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector-Base Voltage	V <sub>CB</sub>	40	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	6.0	Vdc
Base Current - Continuous	I <sub>B</sub>	1.0	Adc
Collector Current - Continuous	I <sub>C</sub>	3.0	Adc
Collector Current - Peak	I <sub>CM</sub>	5.0	Adc
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	MM	C	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Power Dissipation Total P <sub>D</sub> @ T <sub>A</sub> = 25°C (Note 1) Total P <sub>D</sub> @ T <sub>A</sub> = 25°C (Note 2)	P <sub>D</sub>	2.0 0.80	W
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	R <sub>θJC</sub> R <sub>θJA</sub> R <sub>θJA</sub>	11 64 155	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T <sub>L</sub>	260	°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

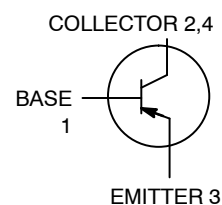
1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.
2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.



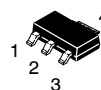
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

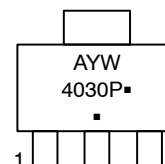
**PNP TRANSISTOR**  
**3.0 AMPERES**  
**40 VOLTS, 2.0 WATTS**



#### MARKING DIAGRAM



**SOT-223**  
**CASE 318E**  
**STYLE 1**



A = Assembly Location  
Y = Year  
W = Work Week  
4030P = Specific Device Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
NJT4030PT1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
NJV4030PT1G		
NJT4030PT3G	SOT-223 (Pb-Free)	4000 / Tape & Reel
NJV4030PT3G		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NJT4030P, NJV4030P

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 0 A <sub>dc</sub> )	V <sub>CEO(sus)</sub>	40	–	–	V <sub>dc</sub>
Emitter–Base Voltage (I <sub>E</sub> = 50 μA <sub>dc</sub> , I <sub>C</sub> = 0 A <sub>dc</sub> )	V <sub>EBO</sub>	6.0	–	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 40 V <sub>dc</sub> )	I <sub>CBO</sub>	–	–	100	nA <sub>dc</sub>
Emitter Cutoff Current (V <sub>BE</sub> = 6.0 V <sub>dc</sub> )	I <sub>EBO</sub>	–	–	100	nA <sub>dc</sub>

### ON CHARACTERISTICS (Note 3)

Collector–Emitter Saturation Voltage (I <sub>C</sub> = 0.5 A <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 1.0 A <sub>dc</sub> , I <sub>B</sub> = 10 mA <sub>dc</sub> ) (I <sub>C</sub> = 3.0 A <sub>dc</sub> , I <sub>B</sub> = 0.3 A <sub>dc</sub> )	V <sub>CE(sat)</sub>	–	–	0.150 0.200 0.500	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = 1.0 A <sub>dc</sub> , I <sub>B</sub> = 0.1 A <sub>dc</sub> )	V <sub>BE(sat)</sub>	–	–	1.0	V <sub>dc</sub>
Base–Emitter On Voltage (I <sub>C</sub> = 1.0 A <sub>dc</sub> , V <sub>CE</sub> = 2.0 V <sub>dc</sub> )	V <sub>BE(on)</sub>	–	–	1.0	V <sub>dc</sub>
DC Current Gain (I <sub>C</sub> = 0.5 A <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 1.0 A <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 3.0 A <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> )	h <sub>FE</sub>	220 200 100	– – –	– 400 –	–

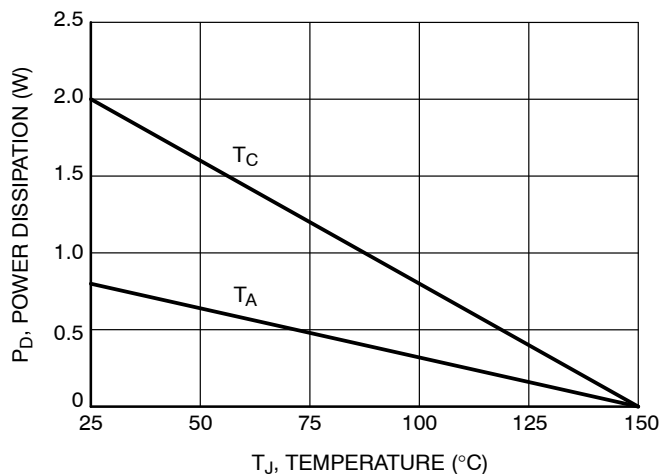
### DYNAMIC CHARACTERISTICS

Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , f = 1.0 MHz)	C <sub>ob</sub>	–	40	–	pF
Input Capacitance (V <sub>EB</sub> = 5.0 V <sub>dc</sub> , f = 1.0 MHz)	C <sub>ib</sub>	–	130	–	pF
Current–Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 10 V, F <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	–	160	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. f<sub>T</sub> = |h<sub>FE</sub>| • f<sub>test</sub>



**Figure 1. Power Derating**

# NJT4030P, NJV4030P

## TYPICAL CHARACTERISTICS

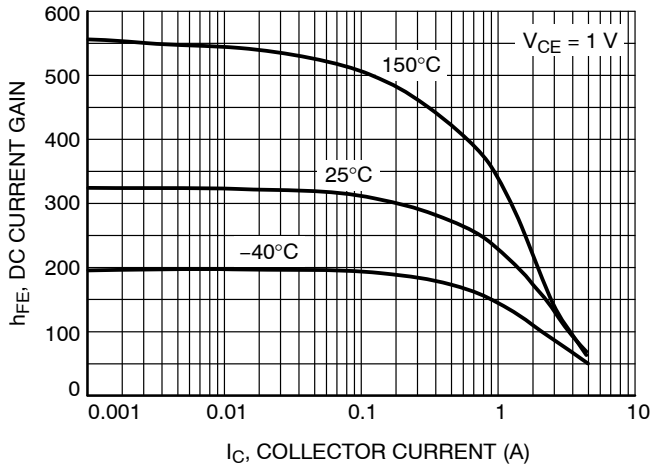


Figure 2. DC Current Gain

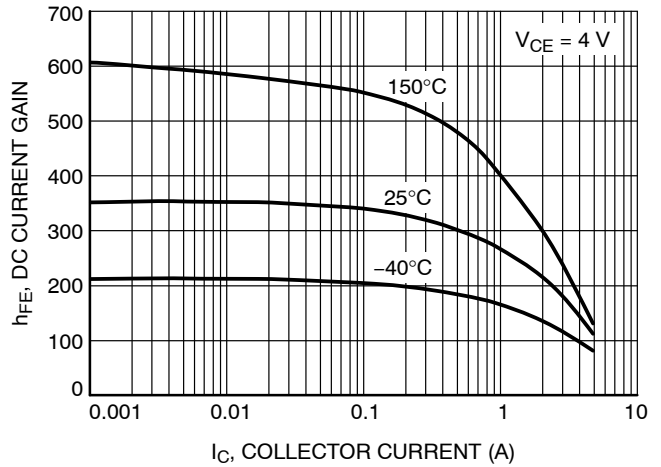


Figure 3. DC Current Gain

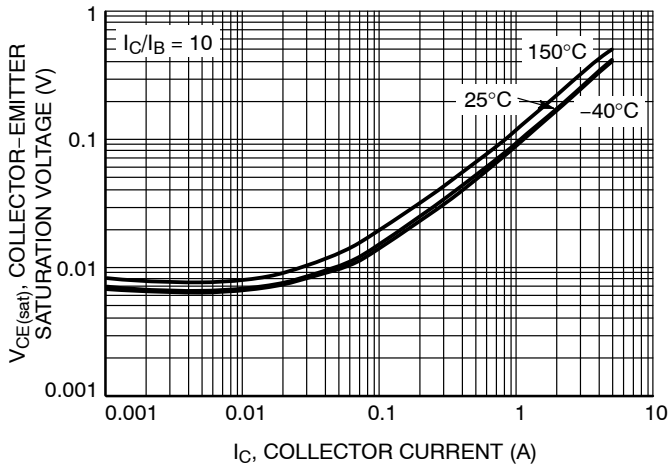


Figure 4. Collector-Emitter Saturation Voltage

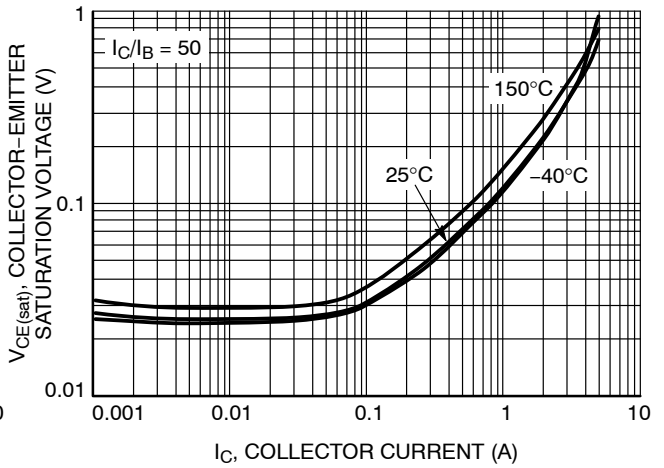


Figure 5. Collector-Emitter Saturation Voltage

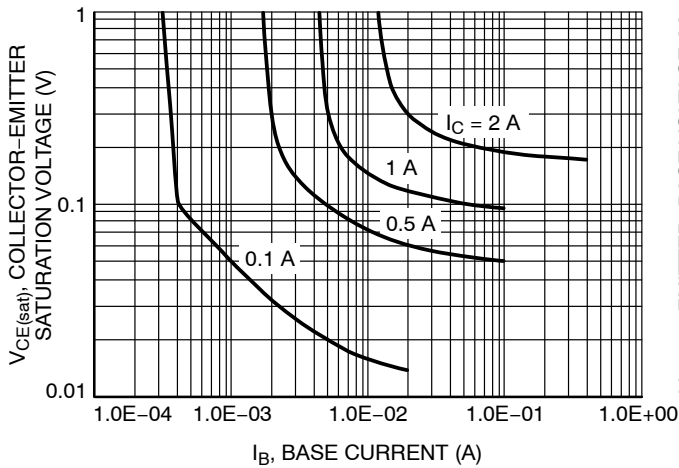


Figure 6. Collector Saturation Region

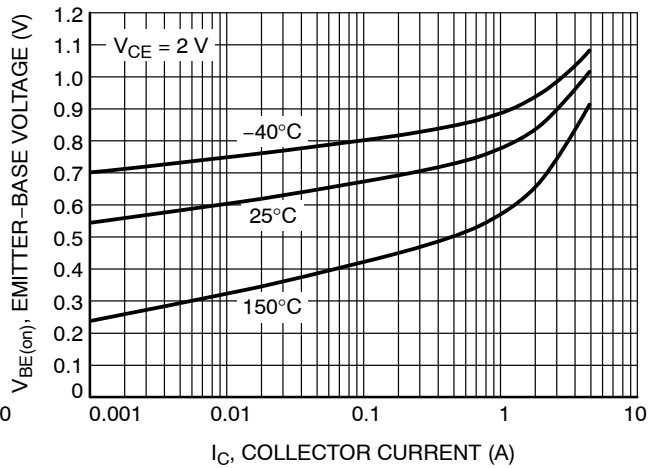


Figure 7.  $V_{BE(on)}$  Voltage

# NJT4030P, NJV4030P

## TYPICAL CHARACTERISTICS

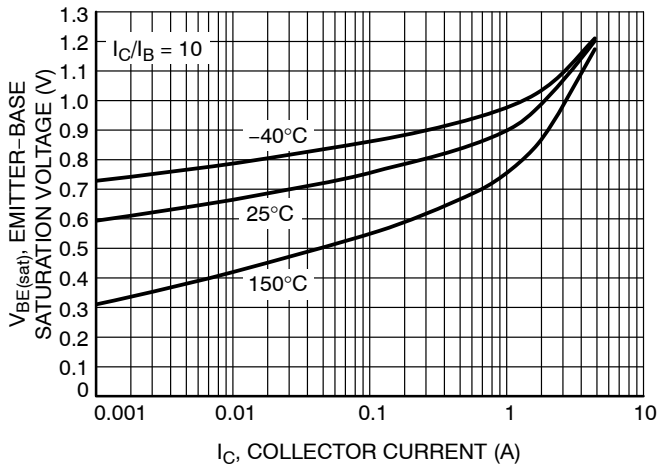


Figure 8. Base-Emitter Saturation Voltage

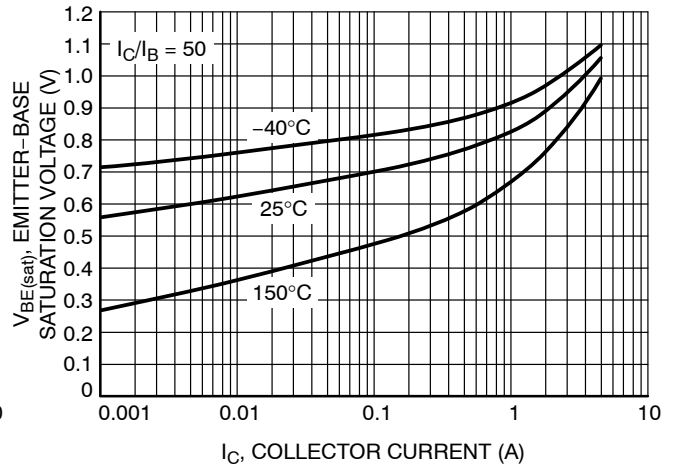


Figure 9. Base-Emitter Saturation Voltage

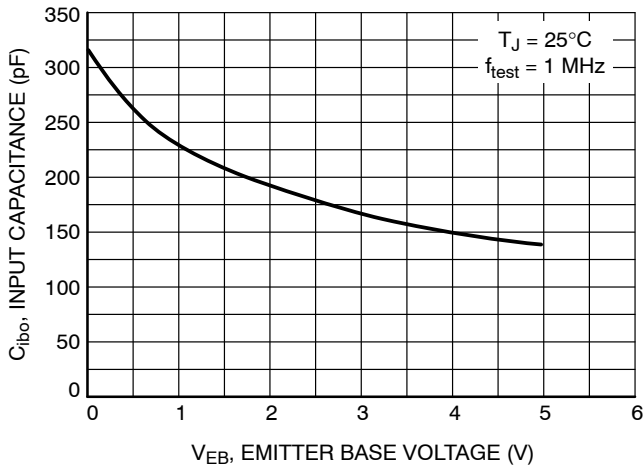


Figure 10. Input Capacitance

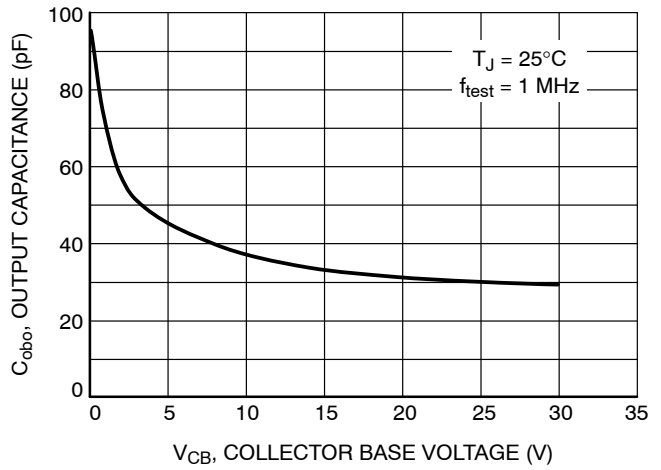


Figure 11. Output Capacitance

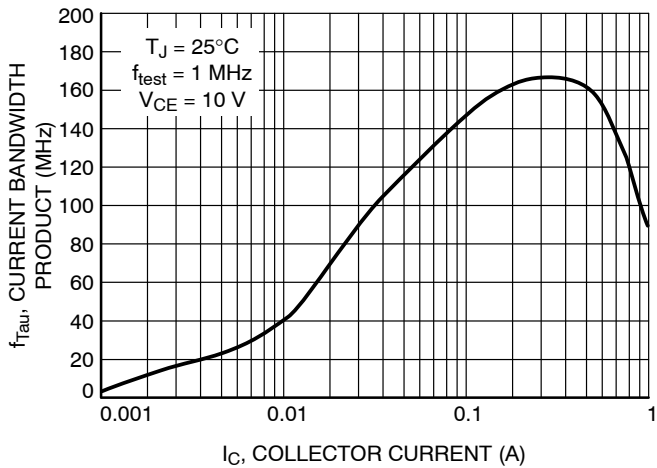


Figure 12. Current-Gain Bandwidth Product

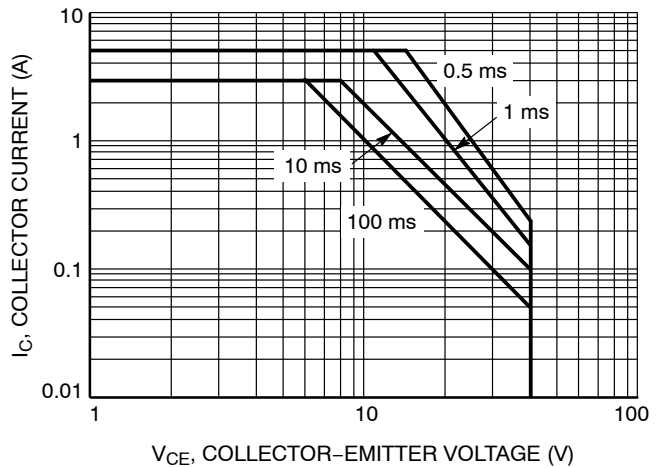


Figure 13. Safe Operating Area

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE R

DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
$\theta$	0°	---	10°



DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT-223 (TO-261)	PAGE 1 OF 2

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**SOT-223 (TO-261)**  
**CASE 318E-04**  
**ISSUE R**

DATE 02 OCT 2018

- |  |   |   |   |   |
|--|---|---|---|---|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. NC<br>4. CATHODE        | <b>STYLE 3:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN           | <b>STYLE 4:</b><br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE<br>4. DRAIN   | <b>STYLE 5:</b><br>PIN 1. DRAIN<br>2. GATE<br>3. SOURCE<br>4. GATE    |
| <b>STYLE 6:</b><br>PIN 1. RETURN<br>2. INPUT<br>3. OUTPUT<br>4. INPUT        | <b>STYLE 7:</b><br>PIN 1. ANODE 1<br>2. CATHODE<br>3. ANODE 2<br>4. CATHODE | <b>STYLE 8:</b><br>CANCELLED  | <b>STYLE 9:</b><br>PIN 1. INPUT<br>2. GROUND<br>3. LOGIC<br>4. GROUND | <b>STYLE 10:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE<br>4. ANODE |
| <b>STYLE 11:</b><br>PIN 1. MT 1<br>2. MT 2<br>3. GATE<br>4. MT 2             | <b>STYLE 12:</b><br>PIN 1. INPUT<br>2. OUTPUT<br>3. NC<br>4. OUTPUT         | <b>STYLE 13:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR |   |   |

**GENERIC  
 MARKING DIAGRAM\***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

<b>DOCUMENT NUMBER:</b>	<b>98ASB42680B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-223 (TO-261)</b>	<b>PAGE 2 OF 2</b>

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at [www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)